





NPN RF TRANSISTOR IN SOT23

Features

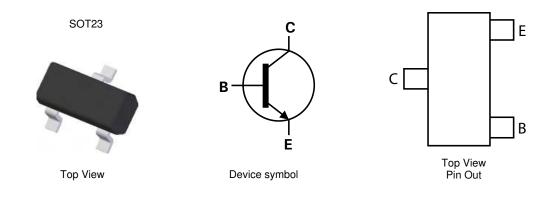
- 3.2GHz unity gain for RF switching applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Applications

RF switch

Mechanical Data

- Case: SOT23
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BFS17NTA	AEC-Q101	E1N	7	8	3,000
BFS17NQTA	Automotive	E1N	7	8	3,000

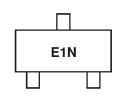
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.

5. For packaging details, go to our website at http://www.diodes.com.

Marking Information



E1N = Product type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	20	V
Collector-Emitter Voltage	V _{CEO}	11	V
Emitter-Base Voltage	V _{EBO}	3	V
Continuous Collector Current	Ι _C	50	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	D	310	mW	
Fower Dissipation	(Note 7)	PD	350	11100	
Thermal Desistance, Junction to Ambient	(Note 6)	D	403	0C/M	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	357	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	R _{0JL}	350	°C/W	
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	100	V	А

6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition; 7. Same as Note 6, expect the device is mounted on 15mm X 15mm X 1.6mm FR4 PCB Notes:

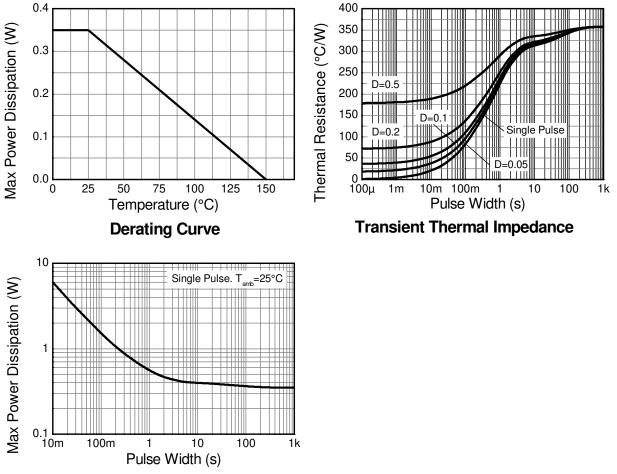
Thermal resistance from junction to solder-point (at the end of the leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.







Thermal Characteristics and Derating information



Pulse Power Dissipation







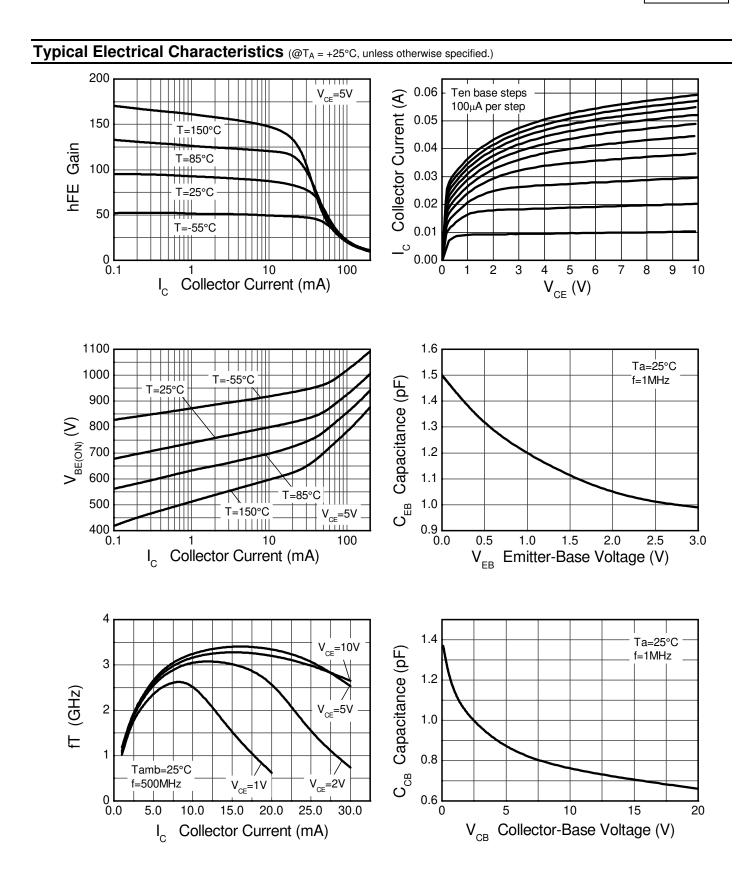
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	20	-	-	V	I _C = 10μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	11	-	-	V	$I_{\rm C} = 1 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	3	-	-	V	I _E = 10μA
Collector Cutoff Current	ICBO	-	-	0.5	μA	$V_{CB} = 10V$
Emitter Cutoff Current	I _{EBO}	-	-	0.5	μA	$V_{EB} = 2V$
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	56	-	180	-	I _C = 5mA, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	-	-	0.5	V	$I_{\rm C} = 25 {\rm mA}, I_{\rm B} = 5 {\rm mA}$
Transition Frequency (Note 10)	f _T	1.4	3.2	-	GHz	$I_E = 25mA, V_{CE} = 5V,$ f = 500MHz
Collector Output Capacitance (Note 10)	C _{ob}	-	0.8	1.5	pF	V _{CB} = 10V, f = 1MHz

Notes: 10. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq 2 \%$







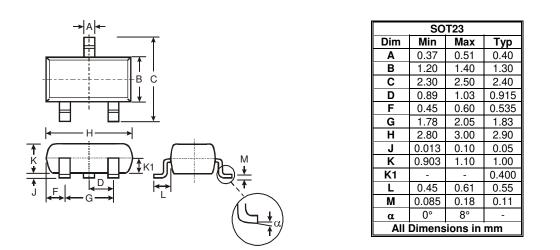






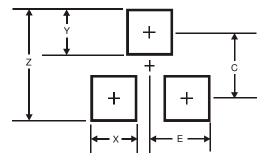
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35





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